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Vishay Semiconductors

Thyristor High Voltage, Phase Control SCR, 50 A



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PRIMARY CHARACTERISTICS					
I _{T(AV)}	50 A				
V _{DRM} /V _{RRM}	1200 V				
V _{TM} (typ.)	1.1 V				
I _{GT} (typ.)	40 mA				
TJ	-40 °C to +150 °C				
Package	TO-247AD 3L				
Circuit configuration	Single SCR				

FEATURES

- Designed and qualified according to JEDEC[®]-JESD 47
- 150 °C maximum operating junction temperature
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>
 Halogen

APPLICATIONS

Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-50TPS12 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications. The glass passivation technology used, has reliable operation up to 150 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
V _{RRM} /V _{DRM}		1200	V			
V _T	50 A, T _J = 125 °C	1.1	v			
I _{T(AV)}		50				
I _{RMS}		79	А			
I _{TSM}		630				
dV/dt		1000	V/µs			
T _J , T _{Stg}		-40 to +150	°C			

VOLTAGE RATINGS							
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA				
VS-50TPS12L-M3	1200	1300	10				



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ABSOLUTE MAXIMUM RATING	S					
DADAMETER	SYMBOL TEST CONDITIONS		VAL			
PARAMETER	STMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum average on-state current	I _{T(AV)}	$T_{C} = 112 \text{ °C}, 180^{\circ} \text{ conduction half sine w}$	ave	-	50	
Maximum continuous RMS on-state current as AC switch	I _{T(RMS)}			-	79	A
Peak, one-cycle non-repetitive surge current		10 ms sine pulse, rated V _{RRM} applied		-	530	
Peak, one-cycle non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied	Initial $T_J = T_J$	-	630	
I ² t for fusing	l ² t	10 ms sine pulse, rated V_{RRM} applied	maximum	-	1405	A ² s
I-t for fushing	141	10 ms sine pulse, no voltage reapplied		-	1986	
I ² √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied	-	19 850	A²√s	
Low level value of threshold voltage	V _{T(TO)1}			-	0.89	V
High level value of threshold voltage	V _{T(TO)2}	T - 125 °C		-	0.97	v
Low level value of on-state slope resistance	r _{t1}	T _J = 125 °C		-	6.77	m 0
High level value of on-state slope resistance	r _{t2}			-	6.32	mΩ
On state veltage	VT	50 A, T _J = 25 °C			1.32	V
On-state voltage	۷Ţ	100 A, T _J = 25 °C	1.4	1.6	v	
Rate of rise of turned-on current	dl/dt	T _J = 25 °C		-	150	A/µs
Holding current	Ι _Η	Analyzing a New Station local T = 05.80		-	300	
Latching current	١L	Anoue supply = 0° , resistive load, $1_j = 2$	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$		350	mA
Poverse and direct lookage ourrest	/	T _J = 25 °C		-	0.05	
Reverse and direct leakage current	I _{RRM} /I _{DRM}	T _J = 125 °C			10	
Rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % V_{DRM} , R	$_{g}-k = \infty \Omega$	-	1000	V/µs

TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS	TYP.	MAX.	UNITS
Peak gate power	P _{GM}	10 ma aina pula	e, no voltage reapplied	-	10	w
Average gate power	P _{G(AV)}	TO THIS SITTLE PUIS	e, no voltage reapplied	-	2.5	vv
Peak gate current	I _{GM}			-	2.5	Α
Peak negative gate voltage	-V _{GM}			-	10	
		$T_J = -40 \ ^\circ C$	Anode supply = 6 V resistive load	-	1.6	v
Required DC gate voltage to trigger	V _{GT}	T _J = 25 °C		-	1.5	v
		T _J = 150 °C		-	1	
		T _J = -40 °C		-	160	
Required DC gate to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	45	100	mA
		T _J = 150 °C		-	60	
DC gate voltage not to trigger	V _{GD}	T 150 °C V	-	0.2	V	
DC gate current not to trigger	I _{GD}	$1_{\rm J} = 150 {}^{\rm 2}{\rm C}, V_{\rm D}$	_{RM} = rated value	-	3	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Turn-on time	t _{gt}	I_T = 50 A, V_D = 50 % $V_{DRM},~I_{gt}$ = 300 mA, T_J = 25 $^\circ C$	1.5	
Turn-off time	t _q	$ I_{T} = 50 \text{ A}, V_{D} = 80 \ \% \ V_{DRM}, \ dV/dt = 20 \ V/\mu s, \ t_{p} = 200 \ \mu s \\ I_{gt} = 100 \ mA, \ dI/dt = 10 \ A/\mu s, \ V_{R} = 100 \ V, \ T_{J} = 150 \ ^{\circ}C $	92	μs

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THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	R SYMBOL TEST CONDITIONS				MAX.	UNITS	
Maximum junction and storage te	emperature range	T _J , T _{Stg}		-40	150	°C	
Maximum thermal resistance, junction to case		R _{thJC}		-	0.35		
Maximum thermal resistance, junction to ambient		R _{thJA}		-	40	°C/W	
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth, and greased	0.2	-		
Mounting to minimum				6	(5)	kgf · cm	
Mounting torque	maximum			12 (10)		(lbf · in)	
Marking device			Case style Super TO-247AD 3L		50TPS12	L	

ARthJ-HS CONDUCTION PER JUNCTION

DEVICE	S	SINE HALF-WAVE CONDUCTION						RECTANGULAR WAVE CONDUCTION			
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-50TPS12L-M3	0.143	0.166	0.208	0.299	0.490	0.099	0.168	0.223	0.311	0.494	°C/W

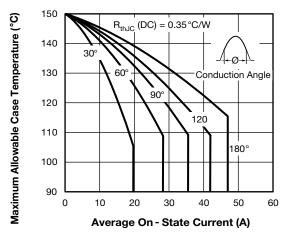


Fig. 1 - Current Rating Characteristics

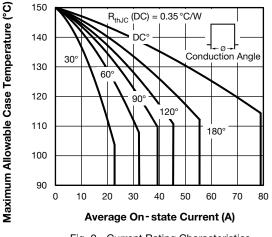


Fig. 2 - Current Rating Characteristics

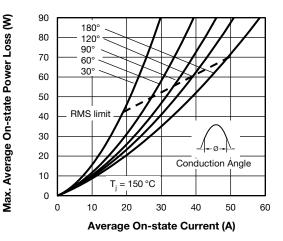


Fig. 3 - On-State Power Loss Characteristics

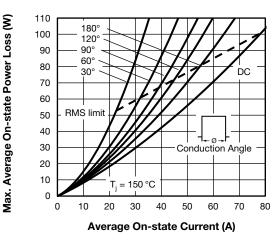


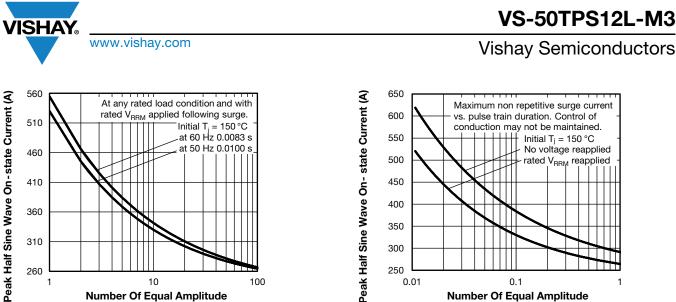
Fig. 4 - On-State Power Loss Characteristics

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Half Cycle Current Pulse (N)

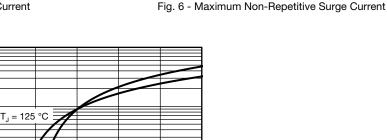
Fig. 5 - Maximum Non-Repetitive Surge Current

1000

100

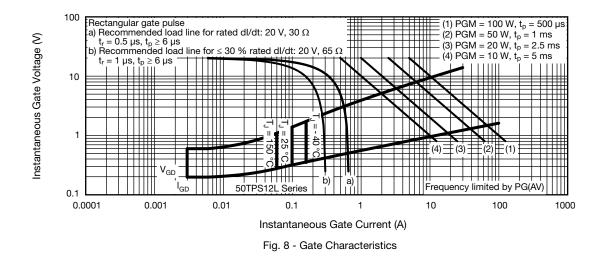
10

Instantaneous On - state Current (A)



T_J = 25 °C 1 0.5 1.0 1.5 2.0 2.5 3.0 Instantaneous On - state Voltage (V)

Fig. 7 - On-State Voltage Drop Characteristics



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Half Cycle Current Pulse (N)

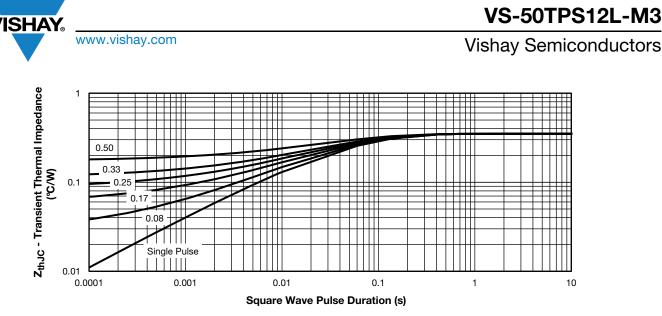


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	50	т	Р	S	12	L	-M3
		2	3	4	5	6	7	8
1 2 3 4 5		Cur Circ T = P = Typ S =	rent coc uit conf thyristo TO-247 e of silio standar	'AD 3L p	50 A) n: backage ery recti	fier		0
7	- [Pac	kage L	= long le gen-free	ead		ant, and	l termin

ORDERING INFORMATION (example)							
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-50TPS12L-M3	25	contact factory	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95626				
Part marking information	www.vishay.com/doc?95007				

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